



Morteza Gholipour

Associate Professor

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Technology, Babol, Iran

EDUCATION

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|---|-------------|
| Ph.D., Electrical and Computer Engineering | 2009 – 2014 |
| University of Tehran, Tehran, Iran | |
| M. S., Electrical and Computer Engineering | 2000 – 2003 |
| University of Tehran, Tehran, Iran | |
| B. S., Electrical Engineering | 1996 – 2000 |
| Ferdowsi University of Mashhad, Mashhad, Iran | |

VISITING RESEARCH

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| Visiting Scholar | December 2012 – August 2013 |
| Coordinated Science Laboratory, University of Illinois at Urbana-Champaign , Champaign, IL, USA | |
| <ul style="list-style-type: none">• Physics-based modeling of the newly proposed graphene-based transistors; compact SPICE modeling.• Released the open-source graphene transistor model on nanohub.org. (1180+ downloads since 2014.)• Performance evaluation compared to conventional CMOS transistors. | |

SKILLS AND LANGUAGES

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- Python, C/C++, HSPICE, Modelsim, Leonardo Spectrum, Tanner L-EDIT, MATLAB, Orcad, Protel, Quartus, Virtual NanoLab, Silvaco TCAD, FPGA tools, Assembly Language Programming, VHDL and Verilog Languages, Visual Basic, Visual C++, Office software tools.
 - Persian (native), English (professional working proficiency)

RESEARCH EXPERIENCE

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| Nanoelectronics and digital system design | 2020 – present |
| <ul style="list-style-type: none">• Memory cell design• Nano device modeling and simulation• Memristor modeling | |
| Modeling and simulation of 2-D material-based devices | 2017 – 2020 |
| <ul style="list-style-type: none">• Compact modeling of TMDFET devices• SPICE compact model of Schottky- and MOS-type GNR-FET devices | |
| Modeling and simulation of crossbar-based nano structures | 2012 – 2017 |
| <ul style="list-style-type: none">• Proposed graphene-based nano-crossbar architecture for electronics circuit design.• Modeling and performance exploration of the nano-crossbar architecture. | |
| Modeling of carbon nanotube as chips interconnects | 2011 – 2012 |
| <ul style="list-style-type: none">• Proposed a compact RC model for multi-walled carbon nanotube interconnects; exploration of buffer insertion and crosstalk effects on the CNT interconnects. | |
| Designing asynchronous logic control | 2002 – 2003 |

- Proposed a low latency asynchronous design scheme; investigation and simulation of different asynchronous logic designs; performance exploration.

WORK EXPERIENCE

Hardware designer and software developer, 2001 – 2005

Research institute for ICT (formerly Iran Telecommunication Research Center), Tehran, Iran

- Implemented management protocol for Synchronous Digital Hierarchy (SDH). **(C++)**
 - Implemented SDH Equipment Management Function (SEMF) interface. **(C++)**
 - Designed and implemented High-Level Data Link Control (HDLC) hardware and firmware for SDH system. **(Verilog)**
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ACADEMIC EXPERIENCE

Faculty Member, Babol Noshirvani University of Technology, Babol, Iran 2014 – present

Deputy, Office of Scientific Collaborations and International Affairs (2023-present)

Visiting Scholar (Advisor: Prof. Deming Chen of University of Illinois at Urbana-Champaign) 2012 – 2013

Advanced VLSI Design, Nanoelectronics, Quantum Electronics, Advanced Digital Electronics, Computer Architecture.

Faculty Member, Azad University of Behshahr, Behshahr, Iran 2005 – 2009

- Lecturer of: C++ programming, Pascal programming, Electronics, Computer Networks, Digital Logic Circuits, Digital System Design Laboratory, Microprocessor laboratory.
- FPGA implementation of the lifting based wavelet transform for image processing applications, using Verilog language.

Reviewer, *IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems*, *IEEE Transactions on Very Large Scale Integration Systems*, *IEEE Transactions on Electron Devices*, *IEEE Transactions on Nanotechnology*, *Microelectronics Journal*, *Journal of Low Power Electronics*, *Journal of Computational Electronics*, *Microelectronics Reliability Journal*, *International Journal of Electronics and Communications*, *International Journal of Circuit Theory and Applications*, *Journal of Emerging Technologies in Computing Systems*.

COURSES TAUGHT

Undergraduate

- Digital systems I (Logic circuits)
- Digital systems II (computer architecture)
- Electronics II
- Pulse technique
- Microprocessors

Graduate

- Advanced digital electronics
 - Advanced VLSI
 - Quantum electronics
 - Nanoelectronics
 - Designing special processors
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PUBLICATIONS

Journal papers

- E. Abbasian, E. Mani, **M. Gholipour**, M. Karamimanesh, M. Sahid, A. Zaidi, "A Schmitt-Trigger-Based Low-Voltage 11 T SRAM Cell for Low-Leakage in 7-nm FinFET Technology," *Circuits, Systems and Signal Processing*, 41, pp. 3081-3105, 2022.
- E. Abbasian, **M. Gholipour**, "Robust transmission gate-based 10T subthreshold SRAM for internet-of-things applications," *Semiconductor Science and Technology*, 37 085013, pp. 1108–1115, 2022.
- E. Gholinataj-Jelodar, A. Aghanejad Ahmadchally, A. Gooran-Shoorakchaly, **M. Gholipour**, "Semi-analytical SPICE-compatible ballistic I–V model for 5 nm channel MoS₂ FETs," *Journal of Computational Electronics*, 21, pp. 1108–1115, 2022.
- E. Abbasian, **M. Gholipour**, "Design of a Highly Stable and Robust 10T SRAM Cell for Low-Power Portable Applications," *Circuits, Systems, and Signal Processing*, vol. 41, pp. 5914–5932, 2022.
- E. Abbasian, S. Birla, **M. Gholipour**, "A 9T high-stable and Low-Energy Half-Select-Free SRAM Cell Design using TMDFETs," *Analog Integrated Circuits and Signal Processing*, 25, pp. 1-9, 2022.
- E. Abbasian, S. Birla, **M. Gholipour**, "Ultra-low-power and stable 10-nm FinFET 10T sub-threshold SRAM," *Microelectronics Journal*, 123, 105427, 2022.
- E. Abbasian, **M. Gholipour**, S. Birla, "A Single-Bitline 9T SRAM for Low-Power Near-Threshold Operation in FinFET Technology," *Arabian Journal for Science and Engineering*, 25, 2022.
- B. Vakili, **M. Gholipour**, "Enhanced overloaded code division multiple access for network on chip," *IET Computers and Digital Techniques*, 16, pp. 45-53, 2021.
- E. Abbasian, **M. Gholipour**, "Single-ended half-select disturb-free 11T static random access memory cell for reliable and low power applications," *International Journal of Circuit Theory and Applications*, 49, pp. 970-989, 2021.
- E. Abbasian, S. Birla and **M. Gholipour**, "A Comprehensive Analysis of Different SRAM Cell Topologies in 7-nm FinFET Technology," *Silicon*, Oct. 2021 <https://doi.org/10.1007/s12633-021-01432-6>.
- E. Abbasian, **M. Gholipour**, F. Izadinasab, "Performance evaluation of GNR-FET and TMD-FET devices in static random access memory cells design," *Int J Circ Theor Appl*. 2021, 49(11), 3630- 3652.
- F. Izadinasab, **M. Gholipour**, "Half-select disturb-free single-ended 9-transistor SRAM cell with bit-interleaving scheme in TMD-FET technology," *Microelectronics Journal*, 113: 105100, 2021.
- E. Abbasian, **M. Gholipour**, "Design of a Schmitt-Trigger-Based 7T SRAM cell for variation resilient Low-Energy consumption and reliable internet of things applications," *AEU-International Journal of Electronics and Communications*, 138:153899-, 2021.
- E. Abbasian, and **M. Gholipour**, "Single-ended half-select disturb-free 11T SRAM cell for reliable and low power applications," to be appeared in *International Journal of Circuit Theory and Application*, 2021.
- A. Gooran-Shoorakchaly, A. Aghanejad Ahmadchally, S. Soleimani-Amiri, and **M. Gholipour**, "Design of a Low-Power Short-Channel Electrostatically-Doped Silicene Nanoribbon FET," to be appeared in *IEEE Transactions on Electron Devices*, 2021.
- A. Aghanejad Ahmadchally, **M. Gholipour**, "Investigation of 6-armchair graphene nanoribbon tunnel FETs," *Journal of Computational Electronics*, 20: 1114 - 1124, 2021.
- E. Mahmoodi, and **M. Gholipour**, "Design space exploration of low-power flip-flops in FinFET technology," *Integration, the VLSI Journal*, vol. 75, pp. 52-62, 2020.
- E. Abbasian, and **M. Gholipour**, "A variation-aware design for storage cells using Schottky-barrier-type GNR-FETs," *Journal of Computational Electronics*, vol. 19, no. 3, pp. 987–1001, 2020.
- A. Rezaei, B. Azizollah-Ganji, **M. Gholipour**, "Effects of the Channel Length on the Nanoscale Field Effect Diode Performance," *Optoelectrical Nanostructures*, vol. 3, no.1, 2018.
- **M. Gholipour**, Y-Y. Chen, and D. Chen, "Compact Modeling to Device- and Circuit-Level Evaluation of Flexible TMD Field-Effect Transistors," *IEEE Transactions on Computer Aided Design*, vol. 37, no. 4, April 2018.
- **M. Gholipour**, "A Compact Short-Channel Model for Symmetric Double-Gate TMD-FET in Subthreshold Region," *IEEE Transactions on Electron Devices*, vol. 64, no.8, pp. 3466-3469, 2017.
- **M. Gholipour**, Y-Y. Chen, A. Sangai, N. Masoumi, and D. Chen, "Analytical SPICE-Compatible Model of Schottky-Barrier-type GNR-FETs with Performance Analysis," *IEEE Transactions on Very Large Scale Integration (VLSI) Systems*,

vol. 24, no. 2, pp. 650-663, Feb. 2016.

- Y-Y. Chen, A. Sangai, A. Rogachev, **M. Gholipour**, G. Iannaccone, G. Fiori, and D. Chen, "A SPICE-Compatible Model of MOS-Type Graphene Nano-Ribbon Field-Effect Transistors Enabling Gate and Circuit-Level Delay and Power Analysis Under Process Variation," *IEEE Transactions on Nanotechnology*, vol. 14, no. 6, Nov. 2015.
- **M. Gholipour**, N. Masoumi, Y-Y. Chen, D. Chen, and M. Pourfath, "Asymmetric Gate Schottky-Barrier Graphene Nanoribbon FETs for Low-Power Design," *IEEE Transactions on Electron Devices*, vol. 61, no. 12, pp. 4000-4006, Dec. 2014.
- **M. Gholipour** and N. Masoumi, "Graphene Nanoribbon Crossbar Architecture for Low Power and Dense Circuit Implementations," *Microelectronics Journal*, Volume 45, Issue 11, November 2014, pp. 1533-1541.
- **M. Gholipour**, and N. Masoumi, "Design investigation of nanoelectronic circuits using crossbar-based nanoarchitectures," *Microelectronics Journal*, Volume 44, Issue 3, March 2013, Pages 190-200.
- **M. Gholipour**, and N. Masoumi, "Efficient Inclusive Analytical Model for Delay Estimation of Multi-Walled Carbon Nanotube Interconnects," *IET Circuits Devices Syst.*, July 2012, Volume 6, Issue 4, p.252-259.
- K. Shojaee, **M. Gholipour**, A. Afzali-Kusha and M. Nourani, "Comparative Study of Asynchronous Pipeline Design Methods", *IEICE Electron. Express*, Vol. 3, No. 8, pp.163-171, (2006).

Conference papers

- Y-Y. Chen, **M. Gholipour**, and D. Chen, "Flexible Transition Metal Dichalcogenide Field-Effect Transistors: A Circuit-Level Simulation Study of Delay and Power under Bending, Process Variation, and Scaling," *Asia and South Pacific Design Automation Conference (ASP-DAC)*, pp.761-768, Jan. 2016.
- H. Sheikhsadi, N. Masoumi, **M. Gholipour**, and M. Rahiminejad, "Time Domain Modeling of Crosstalk Voltage on MWCNT Interconnects," *Iranian Conference on Electrical Engineering (ICEE)*, pp. 1301-1305, Apr. 2015.
- **M. Gholipour**, Y-Y. Chen, A. Sangai, and D. Chen, "Highly Accurate SPICE-Compatible Modeling for Single- and Double-Gate GNR-FETs with Studies on Technology Scaling," *Proceedings of IEEE/ACM Design, Automation & Test in Europe (DATE)*, Dresden, Germany, March 2014.
- Y-Y. Chen, A. Sangai, **M. Gholipour**, and D. Chen, "Graphene Nano-Ribbon Field-Effect Transistors as Future Low-Power Devices," *Low Power Electronics and Design (ISLPED)*, 2013 IEEE International Symposium on, pp. 151-156, 4-6 Sept. 2013.
- Y-Y. Chen, A. Sangai, **M. Gholipour**, and D. Chen, "Schottky-Barrier-Type Graphene Nano-Ribbon Field-Effect Transistors: A Study on Compact Modeling, Process Variation, and Circuit Performance," *2013 IEEE/ACM International Symposium on Nanoscale Architectures (NANOARCH)*, pp. 82-88, Jul. 2013.
- **M. Gholipour**, N. Masoumi, and H. Sheikhsadi, "Analytical Method for Crosstalk Peak Voltage Estimation of MWCNT Interconnects," *21th Iranian Conference on Electric Engineering*, Mashhad, Iran, May 2013.
- **M. Gholipour**, and N. Masoumi, "Efficient Model for Delay Estimation of MWCNT Interconnects," *International Conference on Microelectronics (ICM 2011)*, Tunisia, pp. 1-4, Dec. 2011.
- **M. Gholipour**, and N. Masoumi, "A Comparative Study of Nanowire Crossbar and MOSFET Logic Implementations," *EUROCON-IEEE International Conference on Computer as a Tool*, Lisbon, Portugal, pp. 1-4, 2011.
- **M. Gholipour**, H. Ahmadi Noubari, and M. Kamarei, "A DSP Implementation of Lifting Based DWT for Image Processing Applications," *IEEE ICSIP Int. Conf.*, Dec. 2010, Changsha, China.
- **M. Gholipour**, and H. Ahmadi Noubari, "Hardware Implementation of Lifting Based Wavelet Transform," *IEEE ICSPS Int. Conf.*, Jul. 2010, Dalian, China, vol. 1, pp. 215-219.
- **M. Gholipour**, M. Nourani, D. Edwards, and A. Afzali-Kusha, "LLA: A Low Latency Asynchronous Control with applications," *IEEE ISSCS Int. Conf.*, Jul. 2009, Iasi, Romania, pp. 513-516.
- **M. Gholipour**, A. Afzali-Kusha, and M. Nourani, "A Novel Low Latency Asynchronous Pipeline Control Circuit," *Applied Electronics Intl. Conf.*, Sep. 2008, Pilsen, Czech Republic, pp. 53-55.
- **M. Gholipour**, K. Shojaee, A. Afzali-Kusha, A. Khademzadeh and M. Nourani, "An Efficient Model for Performance Analysis of Asynchronous Pipeline Design Methods," *IEEE ISCAS Conf.*, May 2005, Kobe, Japan, pp. 5234-5237.
- **M. Gholipour**, K. Shojaee, A. Khademzadeh, A. Afzali-Kusha and M. Nourani, "Performance and Power Analysis of Asynchronous Pipeline Design Methods," *16th IEEE ICM Conf.*, December 2004, Tunis, Tunisia.
- **M. Gholipour**, A. Afzali-Kusha, M. Nourani and A. Khademzadeh, "An Efficient Asynchronous Pipeline FIFO for Low-Power Applications," *45th IEEE MWSCAS Conf.*, August 2002, Tulsa, Oklahoma, Vol. 2 pp. 481-484.